

8A, 1200V Hyperfast Diode

The RHRP8120 is a hyperfast diodes with soft recovery characteristics ($t_{rr} < 55\text{ns}$). It has half the recovery time of ultrafast diodes and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

Formerly developmental type TA49096.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RHRP8120	TO-220AC	RHRP8120

NOTE: When ordering, use the entire part number.

Symbol



Features

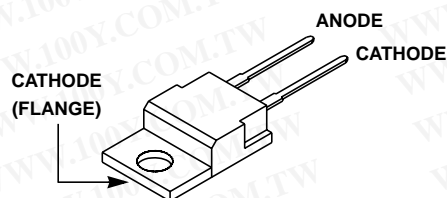
- Hyperfast with Soft Recovery <55ns
- Operating Temperature 175°C
- Reverse Voltage 1200V
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Packaging

JEDEC TO-220AC



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	RHRP8120	UNITS
Peak Repetitive Reverse Voltage	1200	V
Working Peak Reverse Voltage	1200	V
DC Blocking Voltage	1200	V
Average Rectified Forward Current ($T_C = 140^\circ\text{C}$)	8	A
Repetitive Peak Surge Current (Square Wave, 20kHz)	16	A
Nonrepetitive Peak Surge Current (Halfwave, 1 Phase, 60Hz)	100	A
Maximum Power Dissipation	75	W
Avalanche Energy (See Figures 10 and 11)	20	mJ
Operating and Storage Temperature	-65 to 175	°C

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V_F	$I_F = 8\text{A}$	-	-	3.2	V
	$I_F = 8\text{A}$, $T_C = 150^\circ\text{C}$	-	-	2.6	V
I_R	$V_R = 1200\text{V}$	-	-	100	μA
	$V_R = 1200\text{V}$, $T_C = 150^\circ\text{C}$	-	-	500	μA
t_{rr}	$I_F = 1\text{A}$, $dI_F/dt = 200\text{A}/\mu\text{s}$	-	-	55	ns
	$I_F = 8\text{A}$, $dI_F/dt = 200\text{A}/\mu\text{s}$	-	-	70	ns
t_a	$I_F = 8\text{A}$, $dI_F/dt = 200\text{A}/\mu\text{s}$	-	30	-	ns
t_b	$I_F = 8\text{A}$, $dI_F/dt = 200\text{A}/\mu\text{s}$	-	20	-	ns
Q_{RR}	$I_F = 8\text{A}$, $dI_F/dt = 200\text{A}/\mu\text{s}$	-	165	-	nC
C_J	$V_R = 10\text{V}$, $I_F = 0\text{A}$	-	25	-	pF
$R_{\theta JC}$		-	-	2	$^\circ\text{C}/\text{W}$

DEFINITIONS V_F = Instantaneous forward voltage ($p_w = 300\mu\text{s}$, $D = 2\%$). I_R = Instantaneous reverse current. t_{rr} = Reverse recovery time (See Figure 9), summation of $t_a + t_b$. t_a = Time to reach peak reverse current (See Figure 9). t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 9). Q_{RR} = Reverse Recovery Charge. C_J = Junction Capacitance. $R_{\theta JC}$ = Thermal resistance junction to case. p_w = Pulse Width. D = Duty Cycle.

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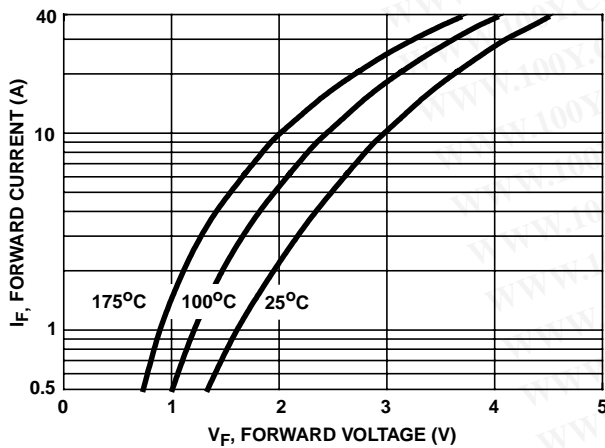
Typical Performance Curves

FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

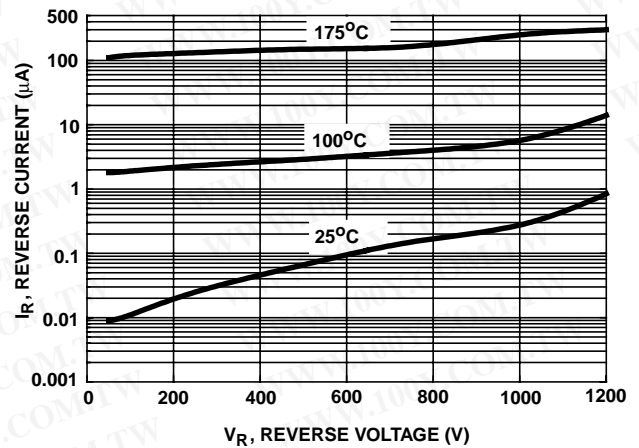


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

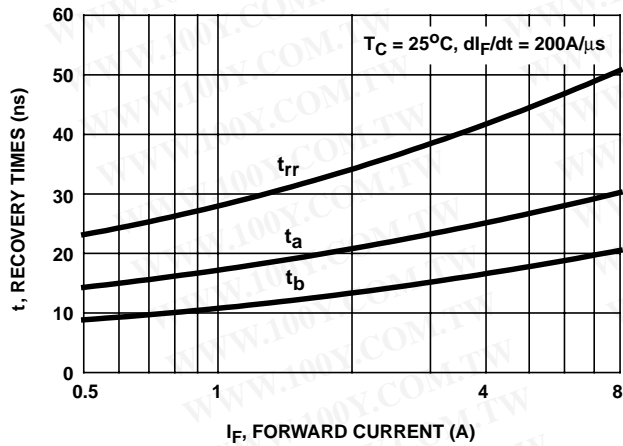
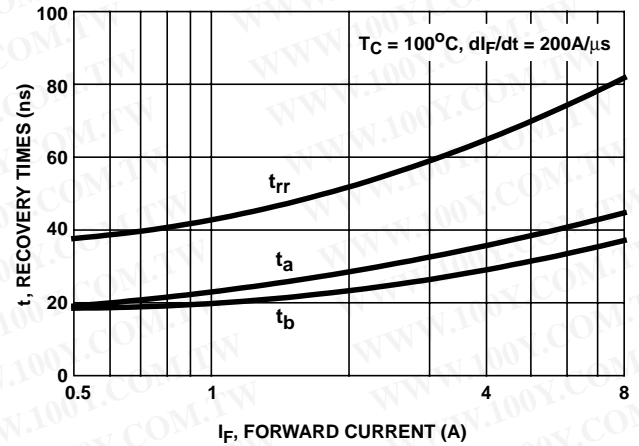
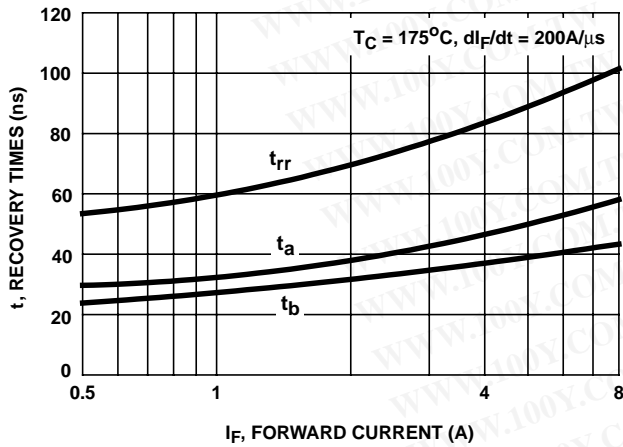
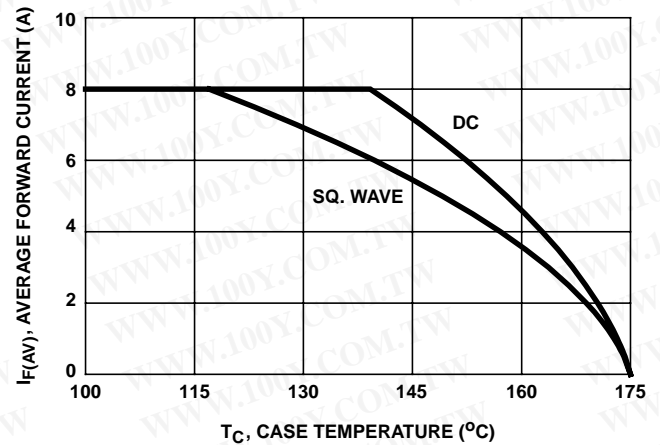
FIGURE 3. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENTFIGURE 4. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENTFIGURE 5. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

FIGURE 6. CURRENT DERATING CURVE

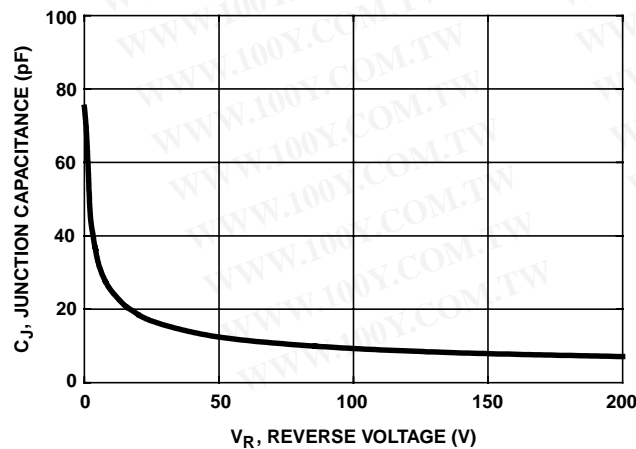


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

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Test Circuits and Waveforms

V_{GE} AMPLITUDE AND
 R_G CONTROL di_F/dt
 t_1 AND t_2 CONTROL I_F

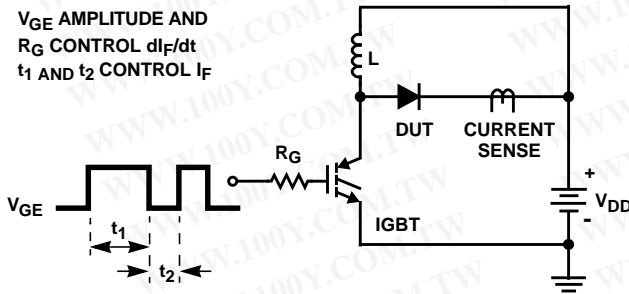


FIGURE 8. t_{rr} TEST CIRCUIT

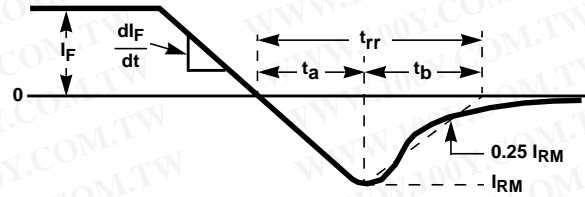


FIGURE 9. t_{rr} WAVEFORMS AND DEFINITIONS

$I_{MAX} = 1A$
 $L = 40mH$
 $R < 0.1\Omega$
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$
 $Q_1 = \text{IGBT (BV}_{CES} > \text{DUT } V_{R(AVL)})$

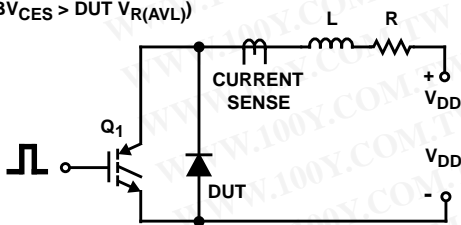


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

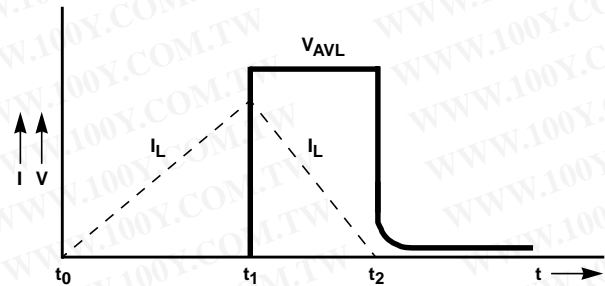


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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